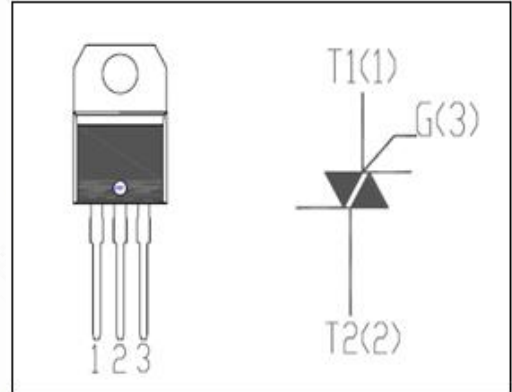


isc Thyristors
BTA12-800BW
DESCRIPTION

- With TO-220 packaging
- Operating in 3 quadrants
- High commutation capability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Solid state relays; heating and cooking appliances
- Switching applications


ABSOLUTE MAXIMUM RATINGS (T_a=25°C)

SYMBOL	PARAMETER		MAX	UNIT
V _{DRM}	Repetitive peak off-state voltage		800	V
V _{RRM}	Repetitive peak reverse voltage		800	V
I _{T(RSM)}	Average on-state current	@T _c =90°C	12	A
I _{TSM}	Surge non-repetitive on-state current	50HZ 60HZ	120 126	A
P _{G(AV)}	Average gate power dissipation (over any 20 ms period)		1.0	W
T _j	Operating junction temperature		-40~125	°C
T _{stg}	Storage temperature		-40~150	°C

ELECTRICAL CHARACTERISTICS (T_c=25°C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS		MIN	MAX	UNIT
I _{RRM}	Repetitive peak reverse current	V _R =V _{RRM} Rated; V _D =V _{DRM} Rated;	T _j =25°C T _j =125°C		0.005 1	mA
I _{DRM}	Repetitive peak off-state current					
V _{TM}	On-state voltage	I _T =17A			1.55	V
I _{GT}	Gate-trigger current	V _D =12V;RG=30 Ω	I		50	mA
			II		50	
			III		50	
V _{GT}	Gate-trigger voltage	V _D =12V;RG=30 Ω			1.3	V
R _{th(j-c)}	Junction to case	Half cycle			2.3	°C/W